



MBRF1035 THRU MBRF10100

Isolation 10.0 AMPS. Schottky Barrier Rectifiers



Voltage Range
35 to 100 Volts
Current
10.0 Amperes

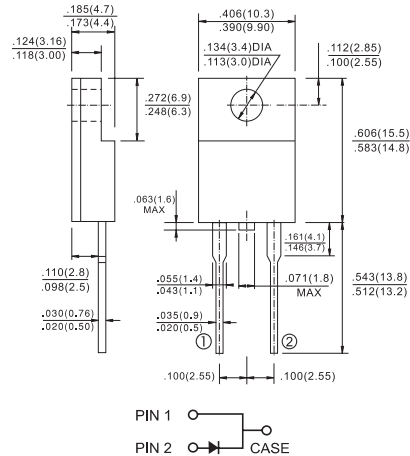
Features

- ✧ Plastic material used carries Underwriters Laboratory Classifications 94V-0
- ✧ Metal silicon junction, majority carrier conduction
- ✧ Low power loss, high efficiency
- ✧ High current capability, low forward voltage drop
- ✧ High surge capability
- ✧ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- ✧ Guardring for overvoltage protection
- ✧ High temperature soldering guaranteed:
260°C/10 seconds, 0.25" (6.35mm) from case

Mechanical Data

- ✧ Cases: ITO-220AC molded plastic body
- ✧ Terminals: Lead solderable per MIL-STD-750, Method 2026
- ✧ Polarity: As marked
- ✧ Mounting position: Any
- ✧ Mounting torque: 5 in. - lbs. max
- ✧ Weight: 0.08 ounce, 2.24 grams

ITO-220AC



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	MBRF 1035	MBRF 1045	MBRF 1050	MBRF 1060	MBRF 1090	MBRF 10100	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	35	45	50	60	90	100	V
Maximum RMS Voltage	V _{RMS}	24	31	35	42	63	70	V
Maximum DC Blocking Voltage	V _{DC}	35	45	50	60	90	100	V
Maximum Average Forward Rectified Current See Fig. 1	I _(AV)	10						A
Peak Repetitive Forward Current (Square Wave, 20KHz) at Tc=135°C	I _{FRM}	20.0						A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	150						A
Peak Repetitive Reverse Surge Current (Note 1)	I _{RRM}	1.0		0.5				A
Voltage Rate of Change (Rated V _R)	dV/dt	10,000						V/μS
Maximum Instantaneous Forward Voltage at (Note 2) I _F =10A, Tc=25°C I _F =10A, Tc=125°C I _F =20A, Tc=25°C I _F =20A, Tc=125°C	V _F	– 0.57 0.84 0.72		0.80 0.70 0.95 0.85		0.85 0.71 – –		V
Maximum Instantaneous Reverse Current @ Tc =25 °C at Rated DC Blocking Voltage (Note 2) @ Tc=125°C	I _R	0.1 15.0				0.1 6.0		mA mA
Typical Junction Capacitance	C _j	390		300		220		pF
Maximum Thermal Resistance, Junction to Case (Note 3)	R θ _{JC}	4.0						°C/W
Operating Junction Temperature Range	T _J	-65 to +150						°C
Storage Temperature Range	T _{STG}	-65 to +175						°C

Notes: 1. 2.0 μs Pulse Width, $f=1.0$ KHz

2. Pulse Test: 300 μs Pulse Width, 1% Duty Cycle

3. Mounted on Heatsink Size of 2 in x 3 in x 0.25 in Al-Plate.

RATINGS AND CHARACTERISTIC CURVES (MBRF1035 THRU MBRF10100)

FIG.1- FORWARD CURRENT DERATING CURVE

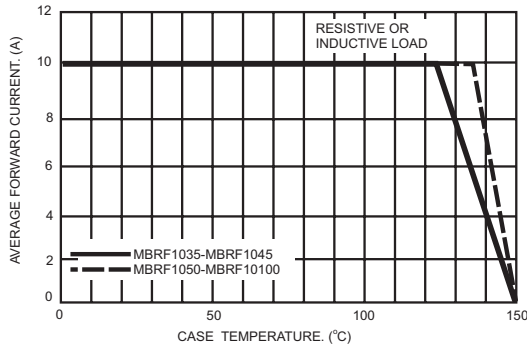


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

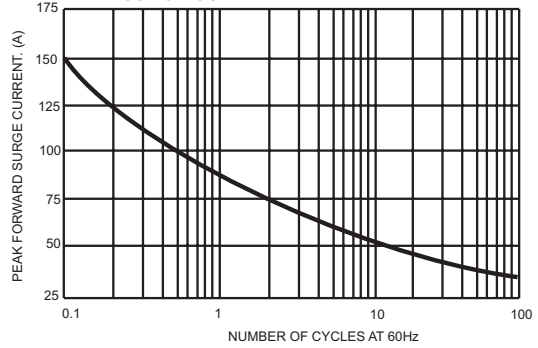


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

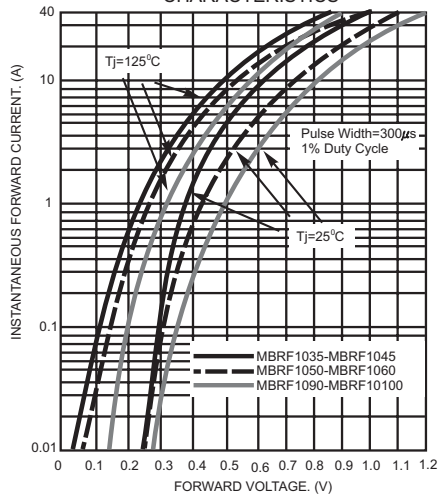


FIG.4- TYPICAL REVERSE CHARACTERISTICS

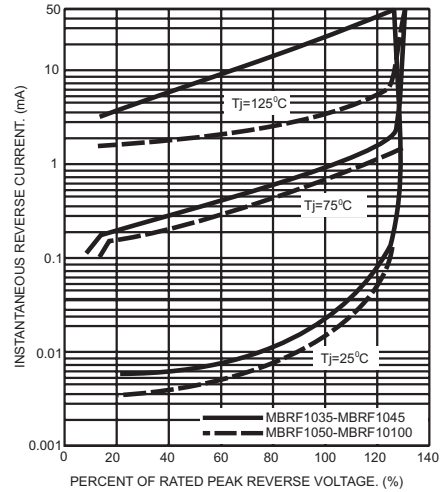


FIG.5- TYPICAL JUNCTION CAPACITANCE

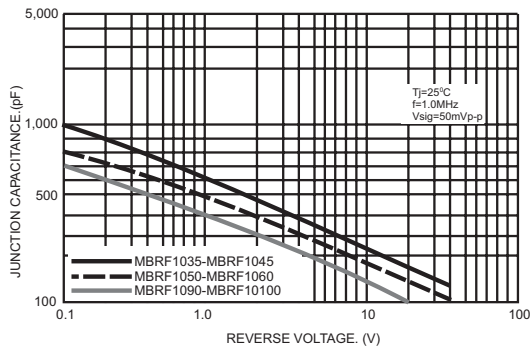


FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS

